

ABSTRACT

A two-beam semiconductor laser device 10 includes: a two-beam semiconductor element LDC having a first and a second semiconductor laser elements LD1 and LD2 that can be driven independently and that are formed integrally on a substrate; and a submount 63 having, mounted on a front part thereof, the two-beam semiconductor laser element LDC with the light-emitting face thereof directed forward and having a first and a second electrode pads 64 and 65 connected to electrodes 61 and 62 of the first and second semiconductor laser element LD1 and LD2 by being kept in contact therewith. The first and second electrode pads 64 and 65 are formed to extend farther behind the two-beam semiconductor laser element LDC, and wires 14 and 16 are wire-bonded behind the two-beam semiconductor laser element LDC.